TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

# **TA7371AFG**

### FM Front-End (1.5V USE)

The TA7371AFG is an FM front end IC designed for low voltage operation (1.5V), which is suitable for stereo headphone radio or radio cassette.

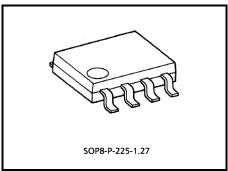
This IC contains RF amplifier, MIX, local oscillator and varactor diode for AFC.

It simplifies the design of front end circuit.

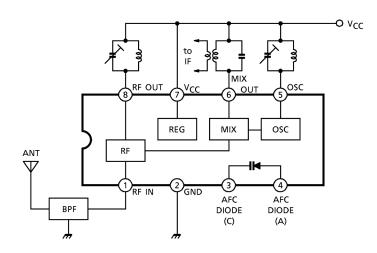
#### Features

- Clamping diode for mixer output.
- Varactor diode for AFC.
- Local OSC. stop voltage: V<sub>CC</sub> = 0.85V (typ.)
- Low quiescent current
  - ICC = 1.8mA (typ.) (VCC = 1.5V, Ta = 25°C)
- Low noise.
- Very few external parts.
- Operating supply voltage range.: VCC = 0.95~5V (Ta = 25°C)

### **Block Diagram**



Weight: 0.08g (typ.)



### **Explanation Of Inner Circuit And Functions**

(1) RF block

The radio signal is applied to RF INPUT passed through the ANT and BPF. This RF block is composed of the common emitter amplifier. The output is designed to be the cascade

connection, because of high sensitivity characteristic, and excellent spurious radiation. (Fig.1)  $\,$ 

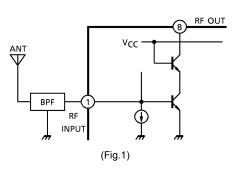
(2) MIX block

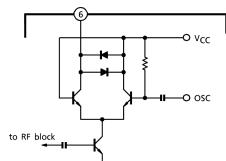
The MIX block is composed of the emitter coupled pair amplifier. (Fig.2)

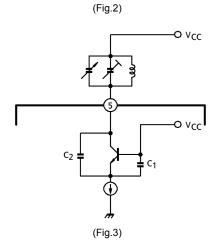
(3) OSC block

OSC block is composed of the colpitts oscillation circuit.

The capacitors  $C_1$  and  $C_2$  are built in this IC.







### Absolute Maximum Ratings (Ta = 25°C)

| Characteristic        | Symbol                | Rating  | Unit |
|-----------------------|-----------------------|---------|------|
| Supply voltage        | V <sub>CC</sub>       | 5       | V    |
| Power dissipation     | P <sub>D</sub> (Note) | 240     | mW   |
| Operating temperature | T <sub>opr</sub>      | -25~75  | °C   |
| Storage temperature   | T <sub>stg</sub>      | -55~150 | °C   |

(Note) Derated above Ta =  $25^{\circ}$ C in the proportion of 2mW / °C.

### **Electrical Characteristics**

(unless otherwise specified,  $V_{CC}$  = 1.5V, Ta = 25°C, f = 83MHz,  $\Delta f$  = ±22.5kHz, f<sub>m</sub> = 1kHz)

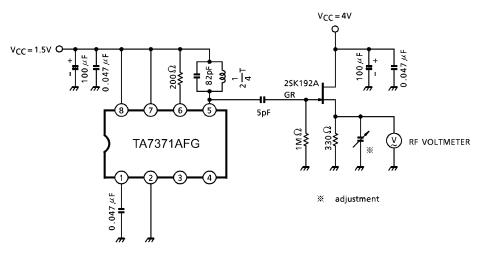
| Characteristic                   | Symbol                | Test<br>Cir–<br>cuit | Test Condition                        | Min. | Тур. | Max. | Unit              |
|----------------------------------|-----------------------|----------------------|---------------------------------------|------|------|------|-------------------|
| Supply current                   | ICC                   | 2                    | V <sub>in</sub> = 0                   | -    | 1.8  | 2.6  | mA                |
| Input limiting sensitivity       | V <sub>in</sub> (lim) | 2                    | -3dB limiting point                   | -    | 10   | 16   | $dB\mu V \; EMF$  |
| Quiescent sensitivity            | QS                    | 2                    | S / N = 30dB                          | _    | 12   | _    | dBµV EMF          |
| Conversion gain                  | G <sub>C</sub>        | 2                    | V <sub>if</sub> = 20mV <sub>rms</sub> | _    | 25   | _    | dB                |
| Local oscillator voltage         | V <sub>osc</sub>      | 1                    | f = 60MHz                             | 75   | 110  | 150  | mV <sub>rms</sub> |
| Local oscillator stop<br>voltage | V <sub>stop</sub>     | 1                    | f = 60MHz                             | _    | 0.85 | 0.95 | V                 |
| AFC diode capacity               | C <sub>AFC</sub>      | 6                    | f = 70MHz, V <sub>AFC</sub> = 3V      | _    | 5.0  | _    | pF                |
| Pin(1) input impedance           | R <sub>ip</sub> 1     | - 3                  | f = 83MHz                             | _    | 300  | _    | Ω                 |
|                                  | C <sub>ip</sub> 1     |                      |                                       | _    | 8.7  | _    | pF                |
| Pin(6) input impedance           | R <sub>op</sub> 2     | 4 f = 10.7MI         | f - 10 7MHz                           | -    | 100  | -    | kΩ                |
|                                  | C <sub>op</sub> 2     |                      |                                       | _    | 3.8  | _    | pF                |
| Pin(8) input impedance           | R <sub>op</sub> 3     | - 5                  | f = 83MHz                             | -    | 2.2  | —    | kΩ                |
|                                  | C <sub>op</sub> 3     |                      |                                       | _    | 4.8  | —    | pF                |

**Terminal Voltage** Terminal Voltage at no Signal ( $V_{CC}$  = 1.5V, Ta = 25°C)

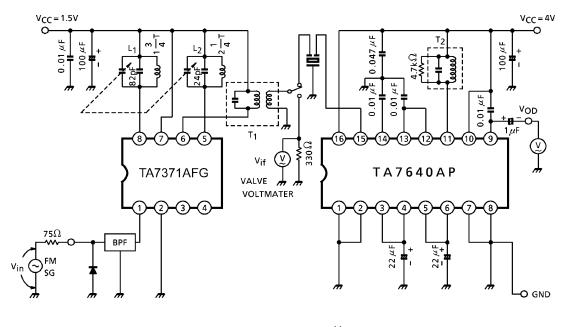
| Terminal No. | Terminal Name       | Terminal Voltage<br>Typ. (V) |  |
|--------------|---------------------|------------------------------|--|
| 1            | RF INPUT            | 0.7                          |  |
| 2            | GND                 | 0                            |  |
| 3            | AFC DIODE (cathode) | —                            |  |
| 4            | AFC DIODE (anode)   | —                            |  |
| 5            | LOCAL OSC           | 1.5                          |  |
| 6            | MIXER OUTPUT        | 1.5                          |  |
| 7            | V <sub>CC</sub>     | 1.5                          |  |
| 8            | RF OUTPUT           | 1.5                          |  |

### **Test Circuit 1**

Vosc, Vstop TEST CIRCUIT



### **Test Circuit 2**



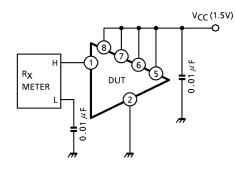
• Conversion gain:  $G_C (dB) = 20 \log \frac{V_{if}}{V_{in}}$ 

### Input / Output Impedance Test Circuit

Input / output impedance and  $\mbox{AFC}$  diode capacity test circuit

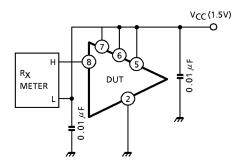
TEST CIRCUIT 3 (R<sub>ip</sub> 1, C<sub>ip</sub> 1)

Pin<sup>(1)</sup> input impedance



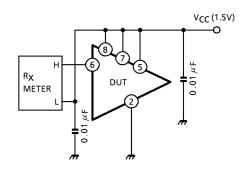
### TEST CIRUCIT 5 (Rop 3, Cop 3)

#### Pin (8) output impedance



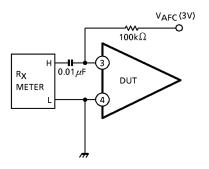
TEST CIRCUIT 4 (R<sub>op</sub> 2, C<sub>op</sub> 2)

Pin(6) output impedance



TEST CIRUCIT 6 (CAFC)

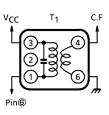
#### AFC diode



### Coil Data For Test Circuit (lower side heterodyne type)

| Coil Name              | f <sub>o</sub> | Qo  | Turn                      | Capacitance        | Comment                                  |
|------------------------|----------------|-----|---------------------------|--------------------|--|
| L <sub>1</sub><br>RF   | 100MHz         | 85  | (1)–(3) 1 <del>3</del> T  | 82pF<br>(external) | Bobbin with ferrite core                 |
| L <sub>2</sub><br>OSC  | 100MHz         | 100 | (1)–(3) 2 <del>1</del> T  | 24pF<br>(external) | Bobbin with ferrite core<br>¢0.5mm UEW   |
| T <sub>1</sub><br>IFT  | 10.7MHz        | 115 | (1)–(3) 12T<br>(4)–(6) 1T | 75pF               | SUMIDA ELECTRIC Co. LTD.<br>0133–309–048 |
| T <sub>2</sub><br>QUAD | 10.7MHz        | 150 | (4)–(6) 14T               | 47pF               | SUMIDA ELECTRIC Co. LTD.<br>44M–037–933A |

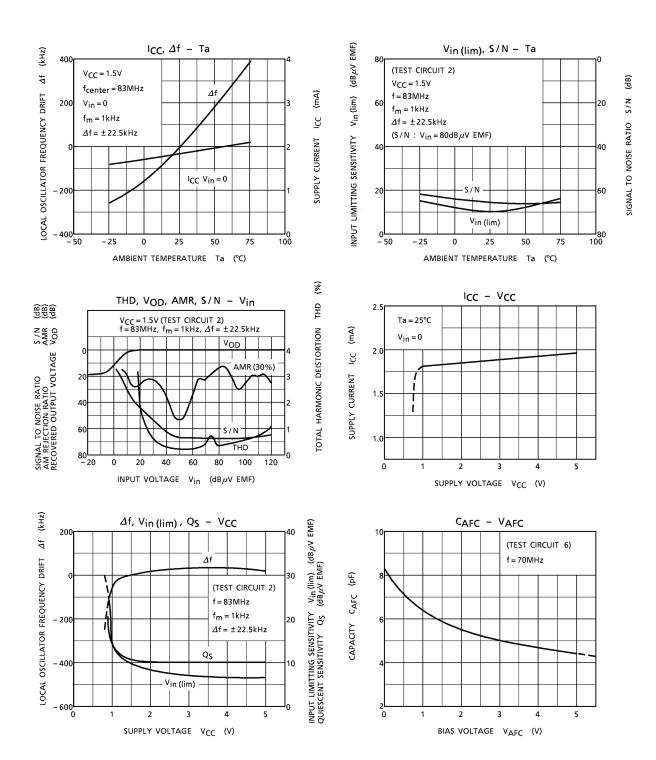
RF BPF SOSHIN ELECTRIC Co. LTD. IF BPF MURATA ELECTRIC Co. LTD. BPW B6A SFE 10.7 MA5





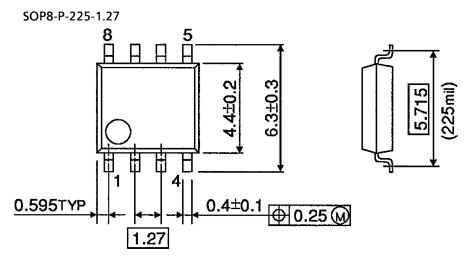
(Bottom view)

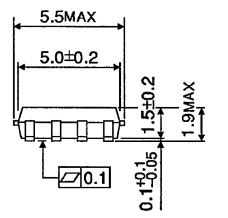
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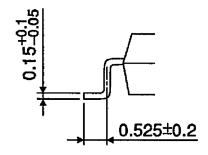


## <u>TOSHIBA</u>

### Package Dimensions







Weight: 0.08g (typ.)

- Use an appropriate power supply fuse to ensure that a large current does not continuously flow in case of over current and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead smoke or ignition. To minimize the effects of the flow of a large current in case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- If your design includes an inductive load such as a motor coil, incorporate a protection circuit into the design to
  prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or
  the negative current resulting from the back electromotive force at power OFF. For details on how to connect a
  protection circuit such as a current limiting resistor or back electromotive force adsorption diode, refer to individual
  IC datasheets or the IC databook. IC breakdown may cause injury, smoke or ignition.
- Use a stable power supply with ICs with built-in protection functions. If the power supply is unstable, the protection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- Carefully select external components (such as inputs and negative feedback capacitors) and load components (such as speakers), for example, power amp and regulator. If there is a large amount of leakage current such as input or negative feedback condenser, the IC output DC voltage will increase. If this output voltage is connected to a speaker with low input withstand voltage, overcurrent or IC failure can cause smoke or ignition. (The over current can cause smoke or ignition from the IC itself.) In particular, please pay attention when using a Bridge Tied Load (BTL) connection type IC that inputs output DC voltage to a speaker directly.

• Over current Protection Circuit

Over current protection circuits (referred to as current limiter circuits) do not necessarily protect ICs under all circumstances. If the Over current protection circuits operate against the over current, clear the over current status immediately. Depending on the method of use and usage conditions, such as exceeding absolute maximum ratings can cause the over current protection circuit to not operate properly or IC breakdown before operation. In addition, depending on the method of use and usage conditions, if over current continues to flow for a long time after operation, the IC may generate heat resulting in breakdown.

• Thermal Shutdown Circuit

Thermal shutdown circuits do not necessarily protect ICs under all circumstances. If the Thermal shutdown circuits operate against the over temperature, clear the heat generation status immediately. Depending on the method of use and usage conditions, such as exceeding absolute maximum ratings can cause the thermal shutdown circuit to not operate properly or IC breakdown before operation.

Heat Radiation Design

When using an IC with large current flow such as power amp, regulator or driver, please design the device so that heat is appropriately radiated, not to exceed the specified junction temperature (Tj) at any time and condition. These ICs generate heat even during normal use. An inadequate IC heat radiation design can lead to decrease in IC life, deterioration of IC characteristics or IC breakdown. In addition, please design the device taking into considerate the effect of IC heat radiation with peripheral components.

Installation to Heat Sink

Please install the power IC to the heat sink not to apply excessive mechanical stress to the IC. Excessive mechanical stress can lead to package cracks, resulting in a reduction in reliability or breakdown of internal IC chip. In addition, depending on the IC, the use of silicon rubber may be prohibited. Check whether the use of silicon rubber is prohibited for the IC you intend to use, or not. For details of power IC heat radiation design and heat sink installation, refer to individual technical datasheets or IC databooks.

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About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-37Pb solder Bath
    - solder bath temperature = 230°C
    - · dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - solder bath temperature = 245°C
    - dipping time = 5 seconds
    - $\cdot$  the number of times = once
    - use of R-type flux